U.S.	DEF	PART	MENT	OF	COM	MERC	Έ
PAT	ENT	AND	TRAD	ЭEМ	ARK	OFFIC	F

## PATENT WITHDRAWAL NOTICE

DATE WITHDRAWN	WITHDRAWAL NUMBER
8/22/08	16550
The following applicati	ion has been WITHDRAWN from the
Tuesday, S	September 02, 2008 issue.
SERIAL NO.	PATENT NUMBER
10/787,120	7,419,889
DRAWINGS	CLASS
019	438/487
TITLE  LASER IRRADIATION METHOD, LASER IRF  MANUFACTURING SEMICONDUCTOR DEV	RADIATION APPARATUS, AND METHOD FOR
LASER IRRADIATION METHOD, LASER IRF MANUFACTURING SEMICONDUCTOR DEV	RADIATION APPARATUS, AND METHOD FOR
LASER IRRADIATION METHOD, LASER IRF MANUFACTURING SEMICONDUCTOR DEV	RADIATION APPARATUS, AND METHOD FOR
LASER IRRADIATION METHOD, LASER IRF MANUFACTURING SEMICONDUCTOR DEV  NAME AND ADDRESS  KOICHIRO TANAKA, ET AL	RADIATION APPARATUS, AND METHOD FOR
LASER IRRADIATION METHOD, LASER IRF MANUFACTURING SEMICONDUCTOR DEV NAME AND ADDRESS KOICHIRO TANAKA, ET AL ATSUGI-SHI, JPX	RADIATION APPARATUS, AND METHOD FOR VICE
LASER IRRADIATION METHOD, LASER IRF MANUFACTURING SEMICONDUCTOR DEV  NAME AND ADDRESS  KOICHIRO TANAKA, ET AL  ATSUGI-SHI, JPX  REASON FOR WITHDRAWAL	RADIATION APPARATUS, AND METHOD FOR VICE
LASER IRRADIATION METHOD, LASER IREMANUFACTURING SEMICONDUCTOR DEVINAME AND ADDRESS  KOICHIRO TANAKA, ET AL ATSUGI-SHI, JPX  REASON FOR WITHDRAWAL  Office of Petitions granted applicant's request to VAPPROVED	RADIATION APPARATUS, AND METHOD FOR VICE
LASER IRRADIATION METHOD, LASER IRRADIATION METHOD, LASER IRREMANUFACTURING SEMICONDUCTOR DEVINAME AND ADDRESS  KOICHIRO TANAKA, ET AL ATSUGI-SHI, JPX  REASON FOR WITHDRAWAL  Office of Petitions granted applicant's request to very serious property of the	RADIATION APPARATUS, AND METHOD FOR VICE

FORM PTO-302 -- (REV. 04-2007)